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($T_C = 25^\circ\text{C}$ unless otherwise noted)

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Collector–Emitter Sustaining Voltage (Note 1) ($I_C = 10\text{ mA}$, $I_B = 0$)	$V_{CEO(sus)}$	250	–	Vdc
Collector Cutoff Current ($V_{CB} = 250\text{ Vdc}$, $I_E = 0$)	I_{CBO}	–	10	μA
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	10	μA

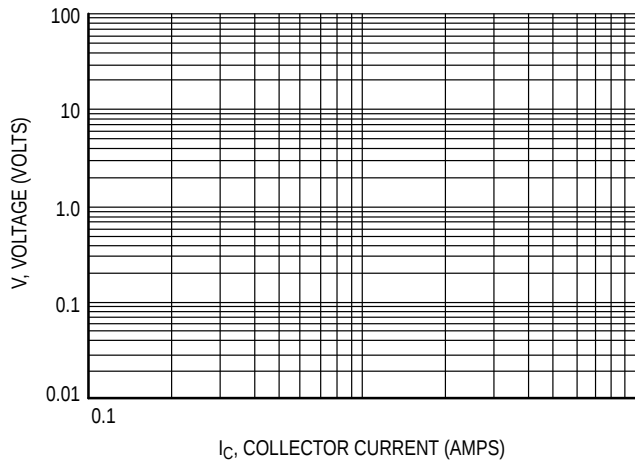
(Note 1)

DC Current Gain ($I_C = 0.5\text{ A}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 1.0\text{ A}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 2.0\text{ A}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	70 50 10	– – –	–
Collector–Emitter Saturation Voltage ($I_C = 1.0\text{ A}$, $I_B = 0.1\text{ A}$)	$V_{CE(sat)}$	–	0.5	Vdc
Base–Emitter On Voltage ($I_C = 1.0\text{ A}$, $V_{CE} = 5.0\text{ Vdc}$)	$V_{BE(on)}$	–	1.0	Vdc

Current Gain – Bandwidth Product (Note 2) ($I_C = 500\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f_{test} = 1.0\text{ MHz}$)	f_T	30	–	MHz
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Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.
2. $f_T = |h_{fe}| \cdot f_{test}$.



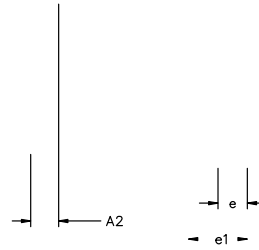


TO-220-3 10.10x15.12x4.45, 2.54P
CASE 221A
ISSUE AL

DATE 05 FEB 2025

A

$\Phi 0.14 \text{ (M)} \text{ C A (M)}$



$\Phi 0.15 \text{ (M)} \text{ C A (M)}$

MILLIMETERS			
DIM	MIN	NOM	MAX
A	4.07	4.45	4.83
A1	1.15	1.28	1.41
A2	2.04	2.42	2.79
b	1.15	1.34	1.52
b1	0.64	0.80	0.96
c	0.36	0.49	0.61
D	9.66	10.10	10.53
D1	8.43	8.63	8.83
E	14.48	15.12	15.75
E1	12.58	12.78	12.98
E2	1.27 REF		

MILLIMETERS			
DIM	MIN	NOM	MAX
e	2.42	2.5	
			J
Q	2.54	2.79	3.04
ϕP	3.60	3.85	4.09
Z	---	---	3.48

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.

Y 1		Y 2		Y 3		Y 4		
1.		1.		1.		1.		1
2.		2.		2.		2.		2
.		.		.		.		2
Y 5		Y 6		Y 7		Y 8		
1.		1.		1.		1.		
2.	U	2.		2.		2.		/ Y
.		.		.		.		
Y 9		Y 10		Y 11		Y 12		
1.		1.		1.		1.		1
2.		2.	U	2.	U	2.		2
.		.	U	.	U	.		

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